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Form PTO 1449 Rev. 7-80 LIST OF PRIOR ART CITED BY APPLICANT (Use Several Sheets If Necessary)			Atty. Docket No. CH8498US	Serial No. To Be Assigned
			Applicant Jagdish Narayan et al	
			Filing Date Herewith	Group No.

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	AC	4,036,708	07/19/77	Feit et al	204	38	
	AD	5,281,485	01/25/94	Colgan et al	428	457	
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